

## **POWER MANAGEMENT**

### **EL Lamp Drivers: Die Specifications**

#### **IMP525**

**Single Cell Battery Powered Electroluminescent Lamp  
Driver/Inverter**

#### **IMP560**

**Power Efficient EL Lamp Driver**

#### **IMP803**

**High-Voltage EL Lamp Driver**

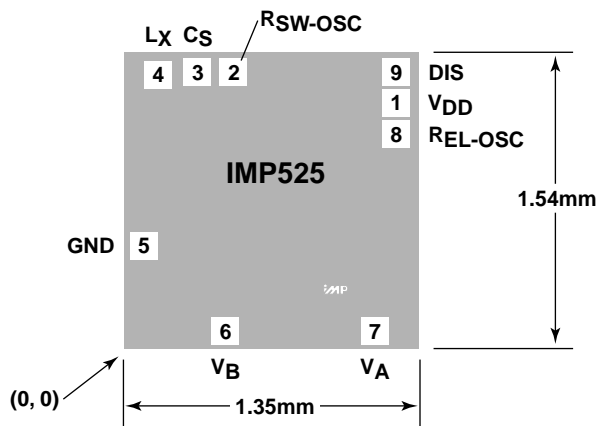
# IMP525 High-Voltage EL Lamp Driver

## General Information

Die Thickness: 25 mils (625 microns)  
 Bond Wire Size: 1.0 mil (25 microns)  
 Back Side Metal: None  
 Back Side Potential: Ground  
 Die Attach Method: Conductive Adhesive  
 Bond Pad Metal: Aluminum, 1% Silicon, 1/2% Copper  
 Bond Pad Size: 100 microns per side  
 Die Size: 1.35mm x 1.54mm

## Pad Description

Pad Number	Name	Function
1	V <sub>DD</sub>	Positive voltage supply.
2	R <sub>SW-OSC</sub>	Switch-mode oscillator frequency setting pad.
3	C <sub>S</sub>	Boost converter storage capacitor pad.
4	L <sub>X</sub>	Inductor pad.
5	GND	Ground pad.
6	V <sub>B</sub>	EL lamp drive.
7	V <sub>A</sub>	EL lamp drive.
8	R <sub>EL-OSC</sub>	EL lamp oscillator frequency setting pad.
9	DIS	Disable pad. DIS = HIGH disables chip.



## Pad Location<sup>1</sup>

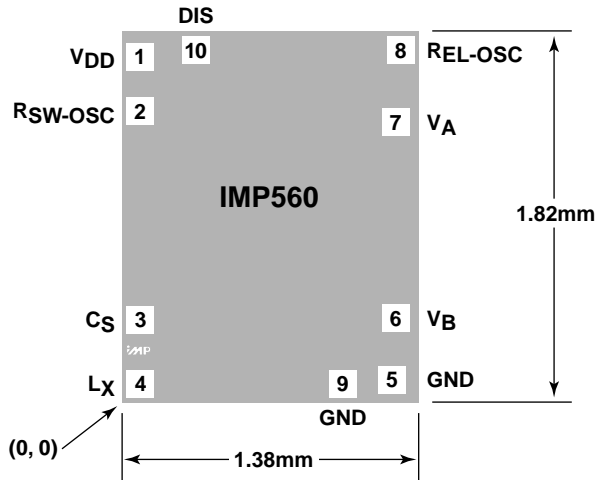
Pad Number	X (microns)	Y (microns)
1	1153	1092
2	476	1226
3	314	1226
4	143	1216
5	111	460
6	397	112
7	1104	112
8	1153	958
9	1153	1226

Notes 1. To bonding pad center

# IMP560 High-Voltage EL Lamp Driver

## General Information

Die Thickness: 25 mils (625 microns)  
 Bond Wire Size: 1.0 mil (25 microns)  
 Back Side Metal: None  
 Back Side Potential: Ground  
 Die Attach Method: Conductive Adhesive  
 Bond Pad Metal: Aluminum, 1% Silicon, 1/2% Copper  
 Bond Pad Size: 100 microns per side  
 Die Size: 1.38mm x 1.82mm



## Pad Description

Pad Number	Name	Function
1	V <sub>DD</sub>	Positive voltage supply.
2	R <sub>SW-OSC</sub>	Switch-mode oscillator frequency setting pad.
3	C <sub>S</sub>	Boost converter storage capacitor pad.
4	L <sub>X</sub>	Inductor pad.
5	GND	Ground pad.
6	V <sub>B</sub>	EL lamp drive.
7	V <sub>A</sub>	EL lamp drive.
8	R <sub>EL-OSC</sub>	EL lamp oscillator frequency setting pad.
9	GND	Ground pin.
10	DIS	Disable pad. DIS = HIGH disables chip.

## Pad Location<sup>1</sup>

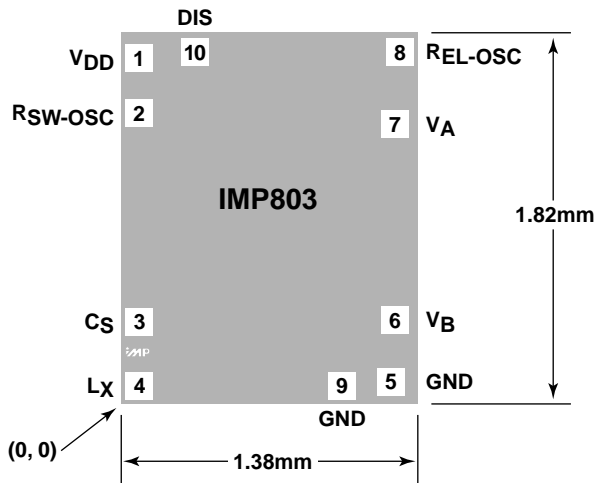
Pad Number	X (microns)	Y (microns)
1	152	1480
2	152	1253.5
3	152	387.75
4	152	122.5
5	1198.5	140
6	1215	395
7	1215	1208.5
8	1234	1508.5
9	998	122.5
10	382	1553.5

Notes 1. To bonding pad center

## IMP803 High-Voltage EL Lamp Driver

### General Information

Die Thickness:	25 mils (625 microns)
Bond Wire Size:	1.0 mil (25 microns)
Back Side Metal:	None
Back Side Potential:	Ground
Die Attach Method:	Conductive Adhesive
Bond Pad Metal:	Aluminum, 1% Silicon, 1/2% Copper
Bond Pad Size:	100 microns per side
Die Size:	1.38mm x 1.82mm



### Pad Description

Pad Number	Name	Function
1	V <sub>DD</sub>	Positive voltage supply.
2	R <sub>SW-OSC</sub>	Switch-mode oscillator frequency setting pad.
3	C <sub>S</sub>	Boost converter storage capacitor pad.
4	L <sub>X</sub>	Inductor pad.
5	GND	Ground pad.
6	V <sub>B</sub>	EL lamp drive.
7	V <sub>A</sub>	EL lamp drive.
8	R <sub>EL-OSC</sub>	EL lamp oscillator frequency setting pad.
9	GND	Ground pin.
10	DIS	Disable pad. DIS = HIGH disables chip.

### Pad Location<sup>1</sup>

Pad Number	X (microns)	Y (microns)
1	152	1480
2	152	1253.5
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6	1215	395
7	1215	1208.5
8	1234	1508.5
9	998	122.5
10	382	1553.5

Notes 1. To bonding pad center



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